

# IEEE EDS Kansai Chapter Awards 2019

## ■ IEEE EDS Kansai Chapter of the Year Award

Author: **Munetaka Noguchi**  
Title: Channel Engineering of 4H-SiC MOSFETs Using Sulphur as a Deep Level Donor  
Coauthors: T. Iwamatsu<sup>1</sup>, H. Amishiro<sup>1</sup>, H. Watanabe<sup>1</sup>, K. Kita<sup>2</sup>, and N. Miura<sup>1</sup>  
Affiliation: 1. Mitsubishi Electric Corporation, 2. The University of Tokyo

## ■ IEEE EDS Kansai Chapter MFSK Award

Author: **Takumi Kawasetsu**  
Title: Flexible Tri-Axis Tactile Sensor Using Spiral Inductor and Magnetorheological Elastomer  
Coauthors: T. Horii, H. Ishihara, and M. Asada  
Affiliation: Osaka University

## ■ IEEE EDS Kansai Chapter IMFEDK Best Paper Award

Author: **Daisuke Tahara**  
Paper-ID: G-6  
Title: Microstructures of  $\epsilon$ -Ga<sub>2</sub>O<sub>3</sub> Thin Film on (100) TiO<sub>2</sub> Substrate by Mist Chemical Vapor Deposition  
Coauthors: H. Nishinaka, Y. Arata, K. Shimazoe, and M. Yoshimoto  
Affiliation: Kyoto Institute of Technology

Author: **Shan Low**  
Paper-ID: G-5  
Title: Impact of SiN Capping during Ohmic Annealing on Performance of GaN-based MISHEMTs  
Coauthors: S. Kawabata, J. Asubar, H. Tokuda and M. Kuzuhara  
Affiliation: University of Fukui